

N-channel 30 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 24 October 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

Quick reference data

Table 1.

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

	QUICK reference uata					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	71	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	58	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 20 A; T _j = 25 °C; see <u>Figure 12</u>	-	6.9	8.1	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; see <u>Figure 12</u>	-	5.5	6.5	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 20 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.6	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 20 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	9	-	nC

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline \\ \hline \\ 1 \end{array} \begin{array}{c} \hline \\ 2 \end{array} \begin{array}{c} \hline \\ 3 \end{array} \begin{array}{c} \hline \\ 4 \end{array}$	mbb076 S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN6R0-30YLB	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669				

4. Limiting values

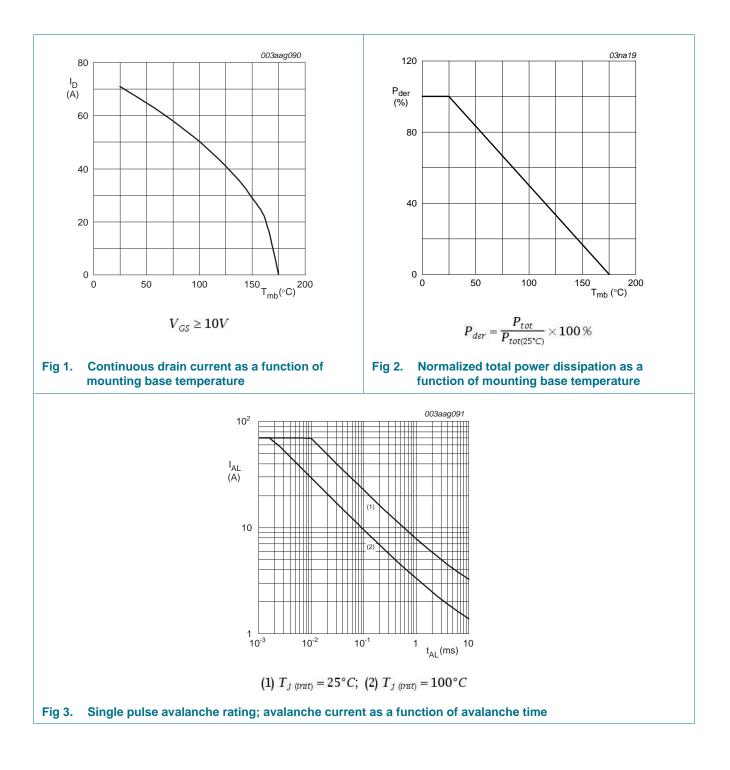
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	71	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	50	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 4	-	283	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	58	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	210	-	V
Source-dra	ain diode				
I _S	source current	T _{mb} = 25 °C	-	53	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	283	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 71 \text{ A}; \\ V_{sup} \leq 30 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \text{ unclamped}; \\ see \underline{\text{Figure 3}} $	-	13	mJ

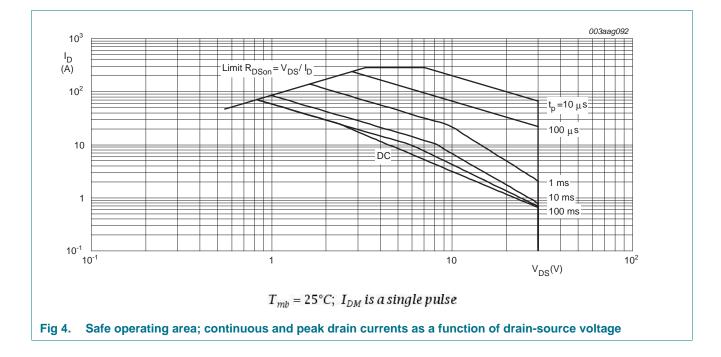
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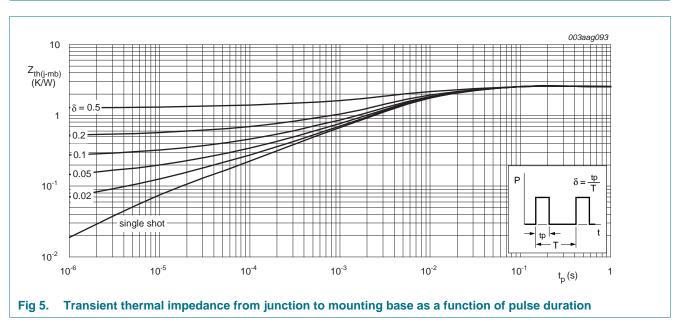
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	2.35	2.57	K/W



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6. Characteristics

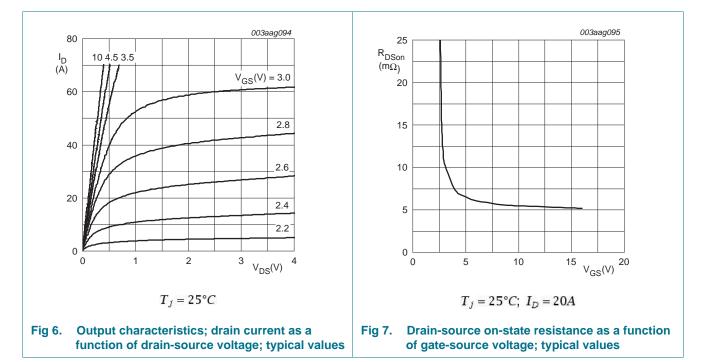
Table 6.	Characteristics			-		
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage		30	-	-	V
		$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 11	1.05	1.48	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 ^\circ\text{C}$	-	-	2.25	V
DSS	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
GSS	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 20 A; T _j = 25 °C; see Figure 12	-	6.9	8.1	mΩ
		V_{GS} = 4.5 V; I_D = 20 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	13.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	5.5	6.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	10.7	mΩ
R _G	gate resistance	f = 1 MHz	-	1.62	3.24	Ω
	characteristics					
Q _{G(tot)} total gate charge	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	19	-	nC
		$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15	-	17	-	nC
Q _{GS}	gate-source charge	I _D = 20 A; V _{DS} = 15 V; V _{GS} = 4.5 V;	-	2.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.6	-	nC
Q _{GD}	gate-drain charge		-	2.6	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.39	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	1088	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see Figure 16}$	-	278	-	pF
C _{rss}	reverse transfer capacitance		-	78	-	pF
	turn-on delay time	$V_{DS} = 15 \text{ V}; \text{ R}_{L} = 0.6 \Omega; \text{ V}_{GS} = 4.5 \text{ V};$	-	16	-	ns
d(on)		$R_{G(ext)} = 4.7 \Omega$		15		ns
	rise time	G(ext) = 4.7 22	-	10	-	
t _{d(on)} t _r t _{d(off)}	rise time turn-off delay time	$r_{G(ext)} = 4.7 \Omega_2$	-	29	-	ns

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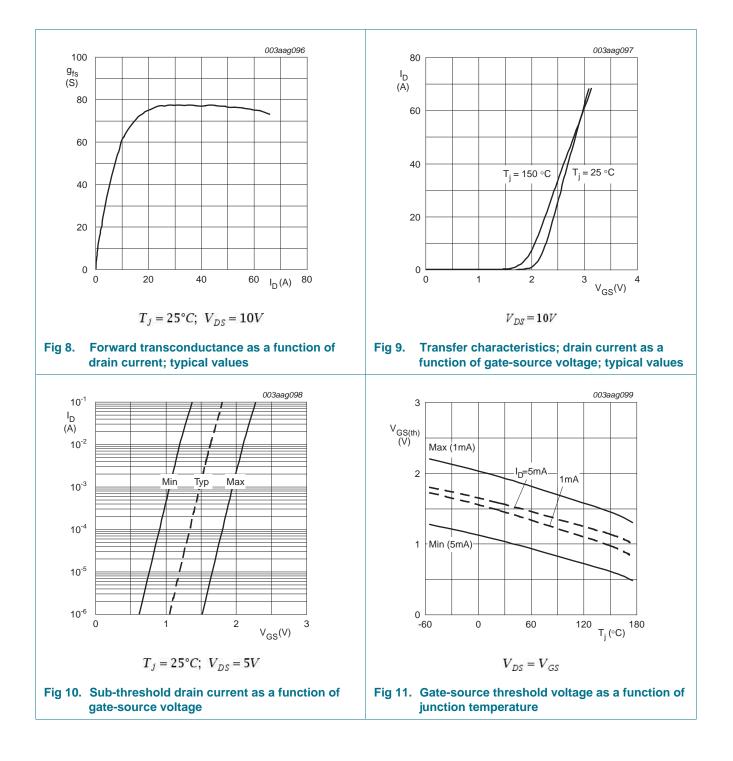
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	7.2	-	nC
Source-dra	ain diode					
V_{SD}	source-drain voltage	I _S = 20 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.85	1.1	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/µs;	-	25.5	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	15	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 V; I_S = 20 A;$	-	15.9	-	ns
t _b	reverse recovery fall time	$dI_S/dt = -100 A/\mu s; V_{DS} = 15 V;$ see Figure 18	-	9.6	-	ns



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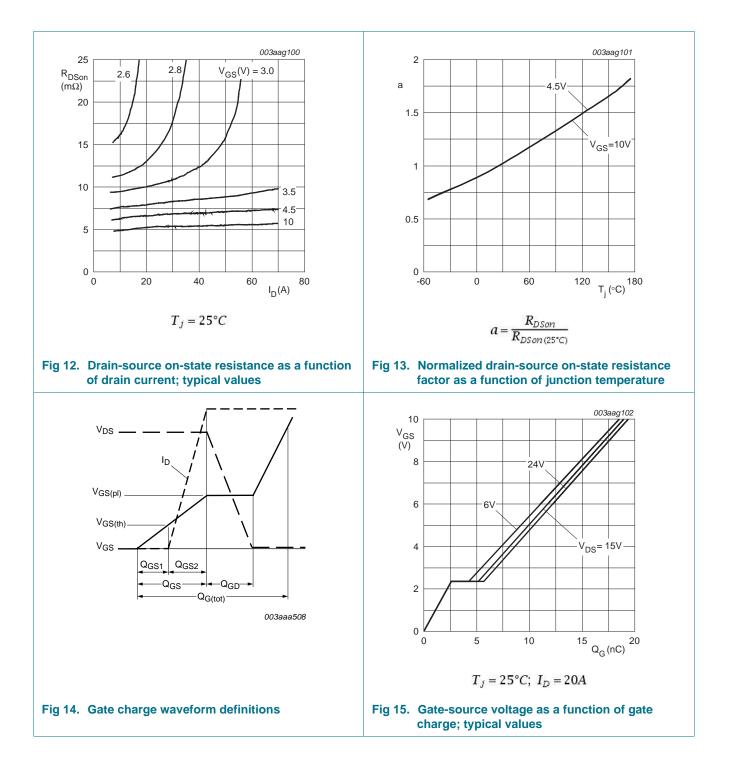
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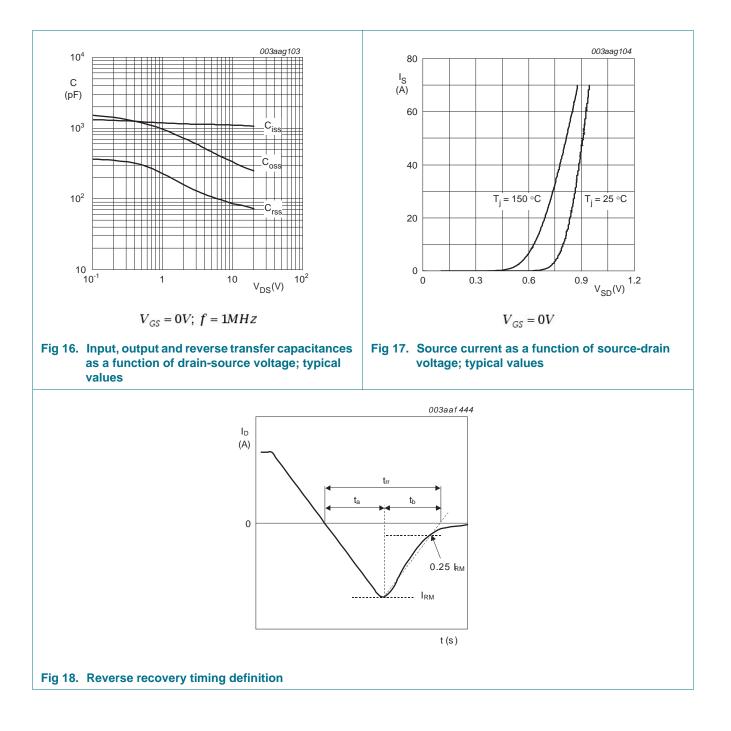
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7. Package outline

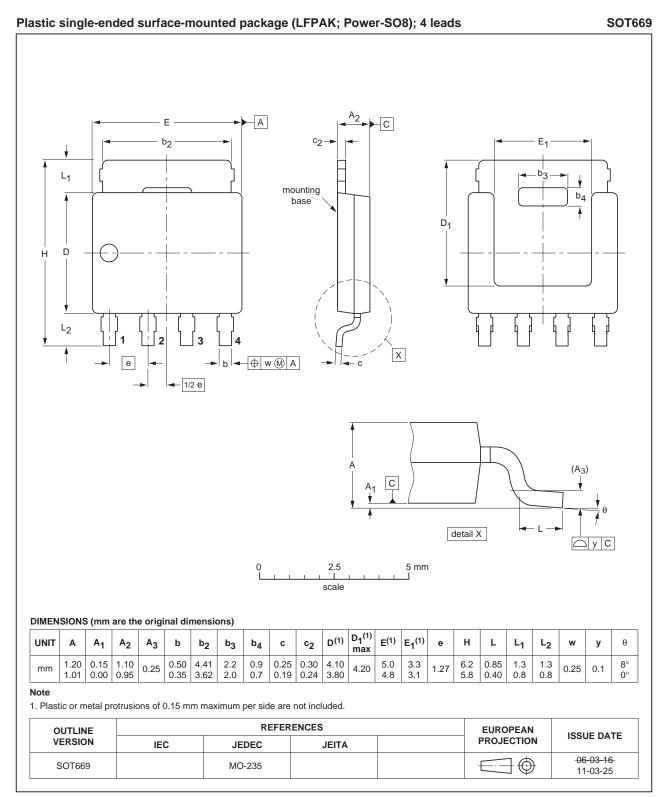


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R0-30YLB v.2	20111024	Product data sheet	-	PSMN6R0-30YLB v.1
Modifications:	 Status changed f 	rom preliminary to product	t.	
	 Various changes 	to content.		
PSMN6R0-30YLB v.1	20110908	Preliminary data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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